



PJS6600

30V Complementary Enhancement Mode MOSFET – ESD Protected

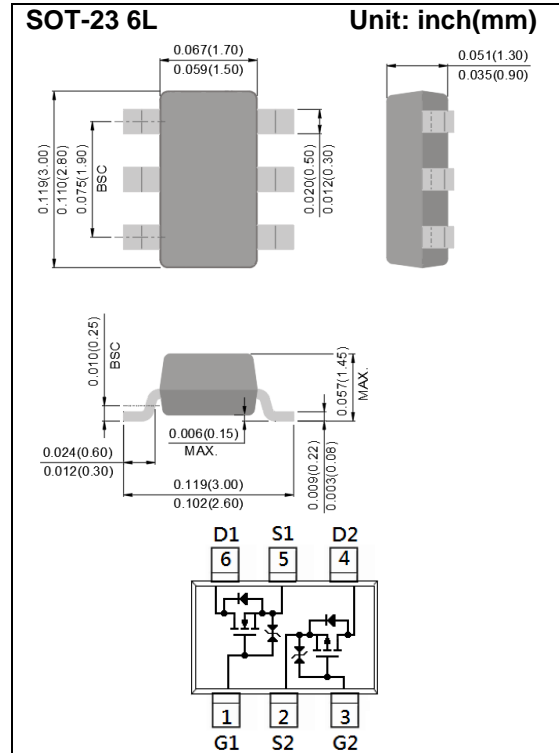
| | | | |
|----------------|------------------|----------------|--------------------|
| Voltage | 30 / -30V | Current | 1.6 / -1.1A |
|----------------|------------------|----------------|--------------------|

Features

- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: SOT-23 6L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0005 ounces, 0.014 grams
- Marking: SC0



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

| PARAMETER | | SYMBOL | N-Ch LIMIT | P-Ch LIMIT | UNITS |
|---|----------------------|-----------------------------------|------------|------------|-------|
| Drain-Source Voltage | | V _{DS} | 30 | -30 | V |
| Gate-Source Voltage | | V _{GS} | ±8 | ±8 | V |
| Continuous Drain Current | | I _D | 1.6 | -1.1 | A |
| Pulsed Drain Current ^(Note 4) | | I _{DM} | 6.4 | -4.4 | A |
| Power Dissipation | T _a =25°C | P _D | 1.25 | | W |
| | Derate above 25°C | | 10 | | mW/°C |
| Operating Junction and Storage Temperature Range | | T _J , T _{STG} | -55~150 | | °C |
| Typical Thermal Resistance - Junction to Ambient ^(Note 3) | | R _{θJA} | 100 | | °C/W |



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N-Channel Electrical Characteristics (T_A=25°C unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNITS |
|---|---------------------|---|------|------|------|-------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D =250uA | 30 | - | - | V |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =250uA | 0.5 | 0.78 | 1.3 | V |
| Drain-Source On-State Resistance | R _{DS(on)} | V _{GS} =4.5V, I _D =1.6A | - | 145 | 200 | mΩ |
| | | V _{GS} =2.5V, I _D =1.1A | - | 185 | 270 | |
| | | V _{GS} =1.8V, I _D =0.2A | - | 330 | 570 | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =30V, V _{GS} =0V | - | 0.01 | 1 | uA |
| Gate-Source Leakage Current | I _{GSS} | V _{GS} =±8V, V _{DS} =0V | - | 1.4 | ±10 | uA |
| Dynamic (Note 5) | | | | | | |
| Total Gate Charge | Q _g | V _{DS} =15V, I _D =1.6A, V _{GS} =4.5V(Note 1,2) | - | 1.5 | - | nC |
| Gate-Source Charge | Q _{gs} | | - | 0.3 | - | |
| Gate-Drain Charge | Q _{gd} | | - | 0.3 | - | |
| Input Capacitance | C _{iss} | V _{DS} =15V, V _{GS} =0V, f=1.0MHZ | - | 93 | - | pF |
| Output Capacitance | C _{oss} | | - | 19 | - | |
| Reverse Transfer Capacitance | C _{rss} | | - | 6 | - | |
| Turn-On Delay Time | t _{d(on)} | V _{DD} =15V, I _D =1.6A, V _{GS} =4.5V, R _G =6Ω(Note 1,2) | - | 6.4 | - | ns |
| Turn-On Rise Time | t _r | | - | 33 | - | |
| Turn-Off Delay Time | t _{d(off)} | | - | 37 | - | |
| Turn-Off Fall Time | t _f | | - | 32 | - | |
| Drain-Source Diode | | | | | | |
| Maximum Continuous Drain-Source Diode Forward Current | I _S | --- | - | - | 1.0 | A |
| Diode Forward Voltage | V _{SD} | I _S = 1.0A, V _{GS} =0V | - | 0.81 | 1.2 | V |

NOTES :

1. Pulse width ≤ 300us, Duty cycle ≤ 2%
2. Essentially independent of operating temperature typical characteristics.
3. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
4. The maximum current rating is package limited.
5. Guaranteed by design, not subject to production testing



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P-Channel Electrical Characteristics (T_A=25°C unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNITS |
|---|---------------------|---|------|-------|------|-------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D =-250uA | -30 | - | - | V |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =-250uA | -0.5 | -0.98 | -1.3 | V |
| Drain-Source On-State Resistance | R _{DS(on)} | V _{GS} =-4.5V, I _D =-1.1A | - | 293 | 370 | mΩ |
| | | V _{GS} =-2.5V, I _D =-0.5A | - | 387 | 540 | |
| | | V _{GS} =-1.8V, I _D =-0.1A | - | 750 | 970 | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =-30V, V _{GS} =0V | - | -0.01 | -1 | uA |
| Gate-Source Leakage Current | I _{GSS} | V _{GS} =±8V, V _{DS} =0V | - | ±3.4 | ±10 | uA |
| Dynamic (Note 5) | | | | | | |
| Total Gate Charge | Q _g | V _{DS} =-15V, I _D =-1.1A, V _{GS} =-4.5V (Note 1,2) | - | 1.6 | - | nC |
| Gate-Source Charge | Q _{gs} | | - | 0.5 | - | |
| Gate-Drain Charge | Q _{gd} | | - | 0.3 | - | |
| Input Capacitance | C _{iss} | V _{DS} =-15V, V _{GS} =0V, f=1.0MHZ | - | 125 | - | pF |
| Output Capacitance | C _{oss} | | - | 22 | - | |
| Reverse Transfer Capacitance | C _{rss} | | - | 6 | - | |
| Turn-On Delay Time | td _(on) | V _{DD} =-15V, I _D =-1.1A, V _{GS} =-4.5V, R _G =6Ω (Note 1,2) | - | 11 | - | ns |
| Turn-On Rise Time | tr | | - | 51 | - | |
| Turn-Off Delay Time | td _(off) | | - | 65 | - | |
| Turn-Off Fall Time | tf | | - | 46 | - | |
| Drain-Source Diode | | | | | | |
| Maximum Continuous Drain-Source Diode Forward Current | I _S | --- | - | - | -1.0 | A |
| Diode Forward Voltage | V _{SD} | I _S =-1.0A, V _{GS} =0V | - | -0.9 | -1.2 | V |

NOTES :

1. Pulse width ≤ 300us, Duty cycle ≤ 2%
2. Essentially independent of operating temperature typical characteristics.
3. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
4. The maximum current rating is package limited.
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N-Channel TYPICAL CHARACTERISTIC CURVES

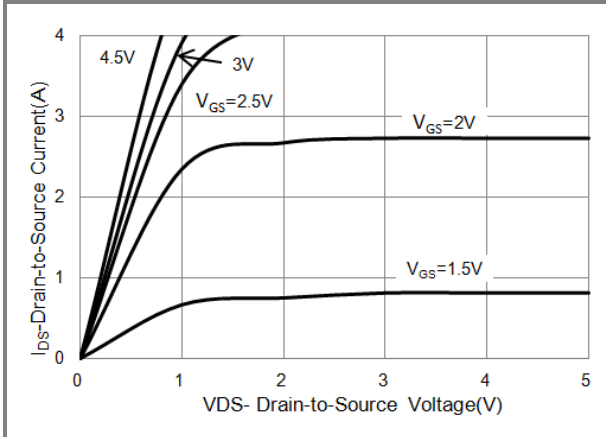


Fig.1 On-Region Characteristics

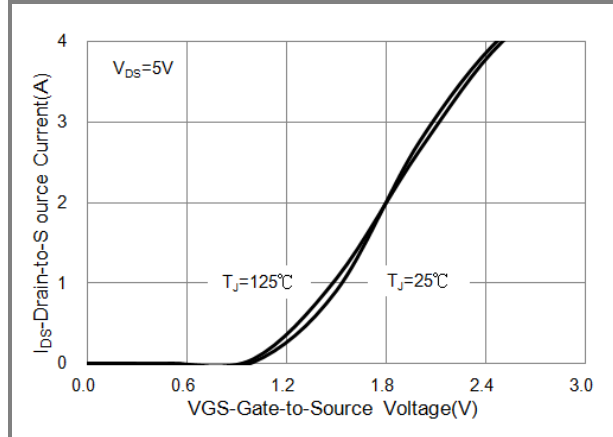


Fig.2 Transfer Characteristics

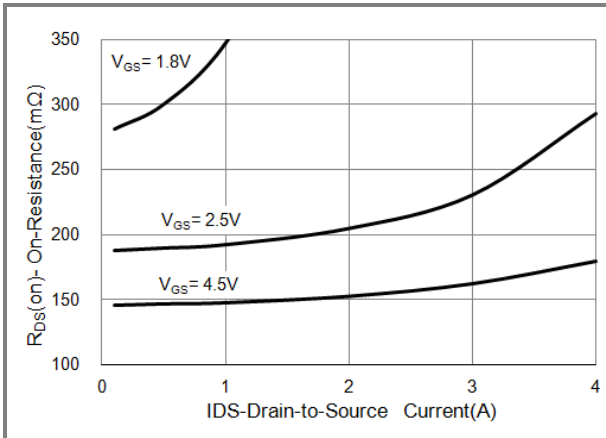


Fig.3 On-Resistance vs. Drain Current

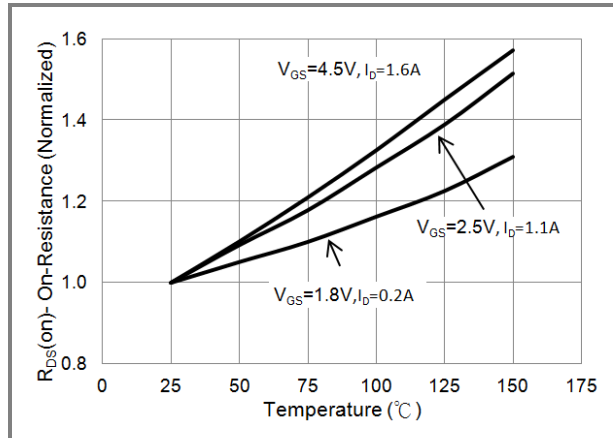


Fig.4 On-Resistance vs. Junction temperature

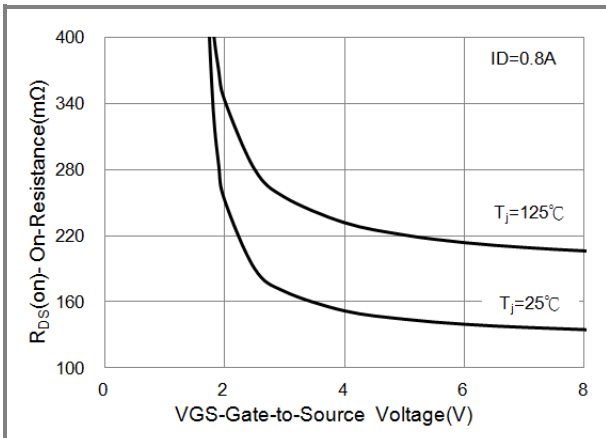


Fig.5 On-Resistance Variation with VGS.

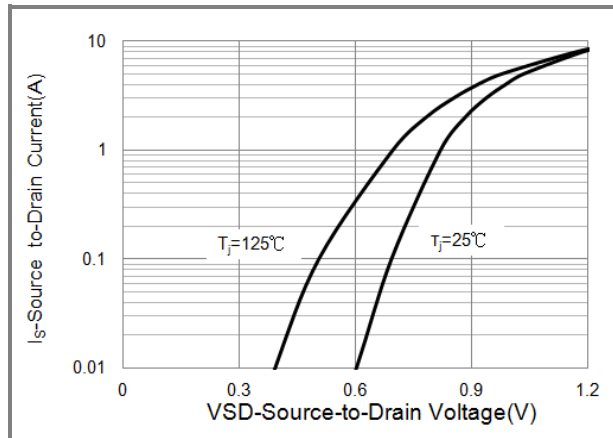


Fig.6 Body Diode Characteristics



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N-Channel TYPICAL CHARACTERISTIC CURVES

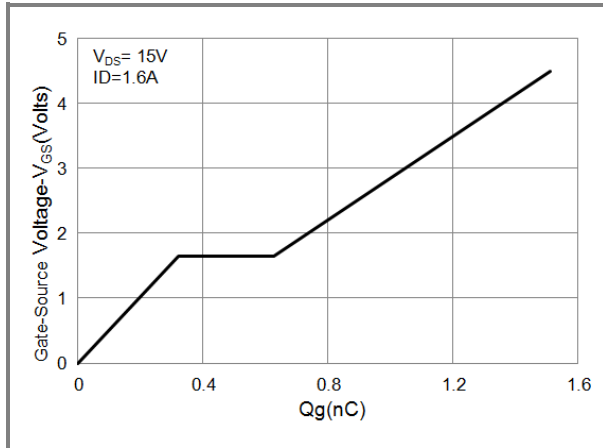


Fig.7 Gate-Charge Characteristics

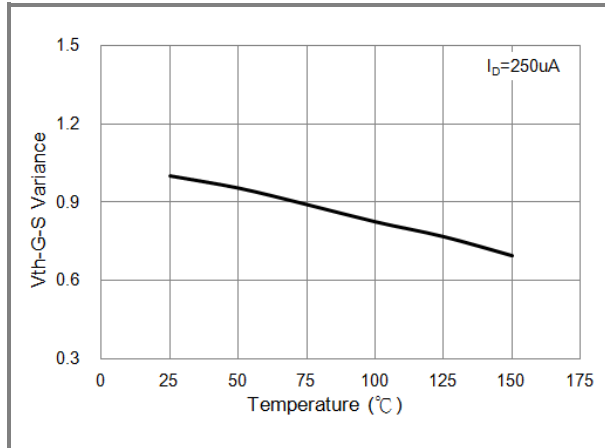


Fig.8 Threshold Voltage Variation with Temperature.

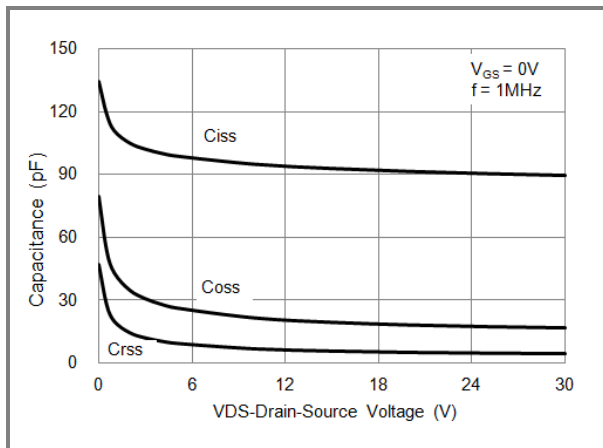


Fig.9 Capacitance vs. Drain-Source Voltage.



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P-Channel TYPICAL CHARACTERISTIC CURVES

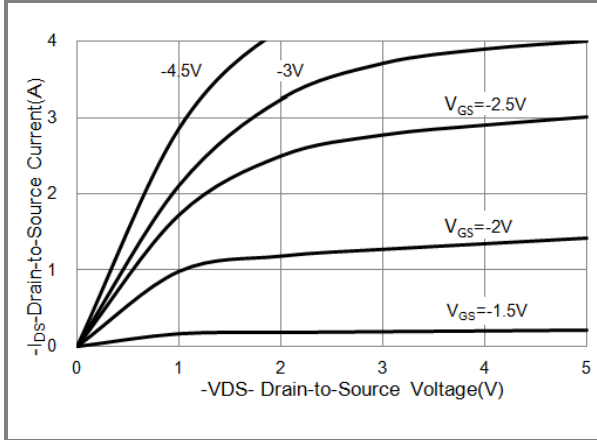


Fig.1 On-Region Characteristics

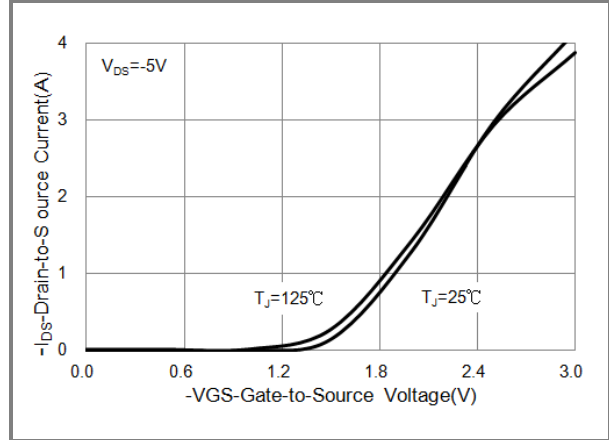


Fig.2 Transfer Characteristics

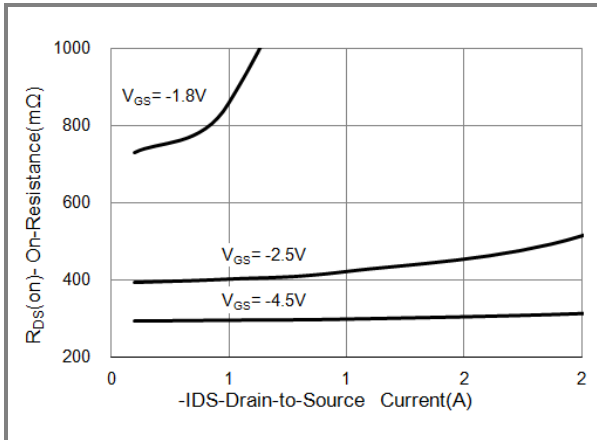


Fig.3 On-Resistance vs. Drain Current

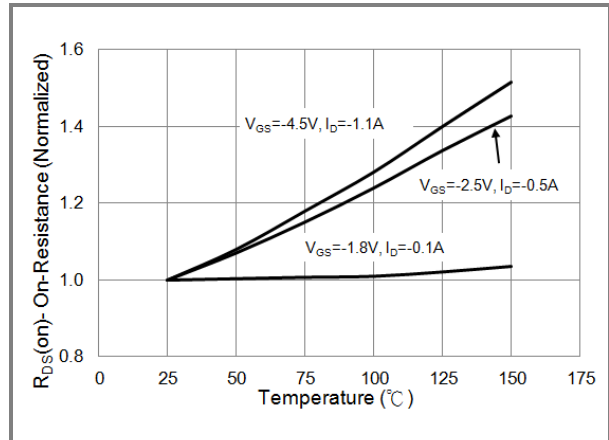


Fig.4 On-Resistance vs. Junction temperature

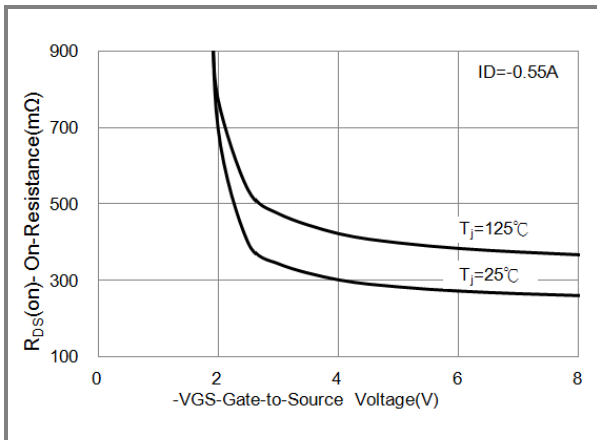


Fig.5 On-Resistance Variation with VGS.

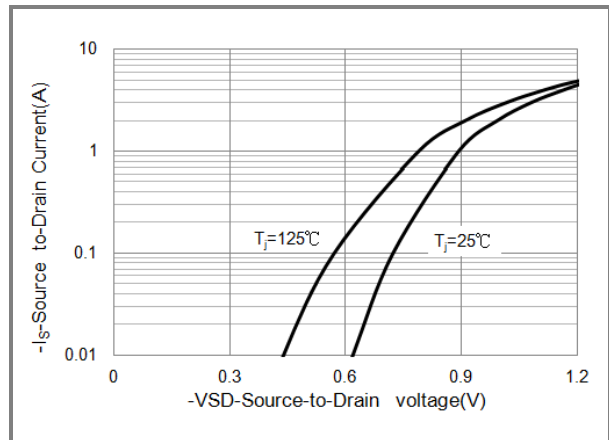


Fig.6 Body Diode Characteristic



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P-Channel TYPICAL CHARACTERISTIC CURVES

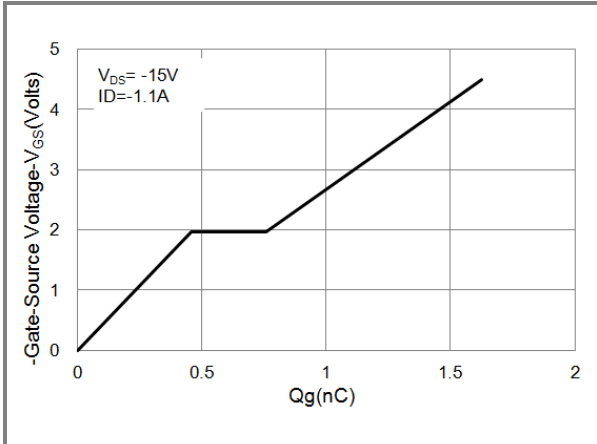


Fig.7 Gate-Charge Characteristics

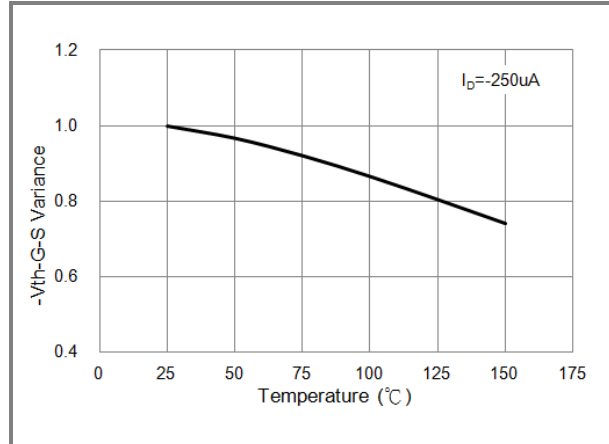


Fig.8 Threshold Voltage Variation with Temperature.

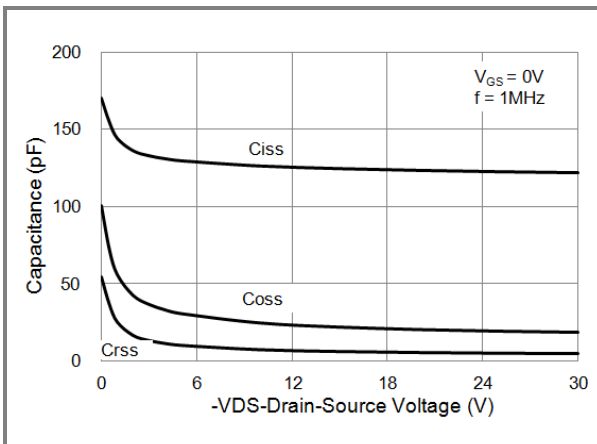


Fig.9 Threshold Voltage Variation with Temperature.

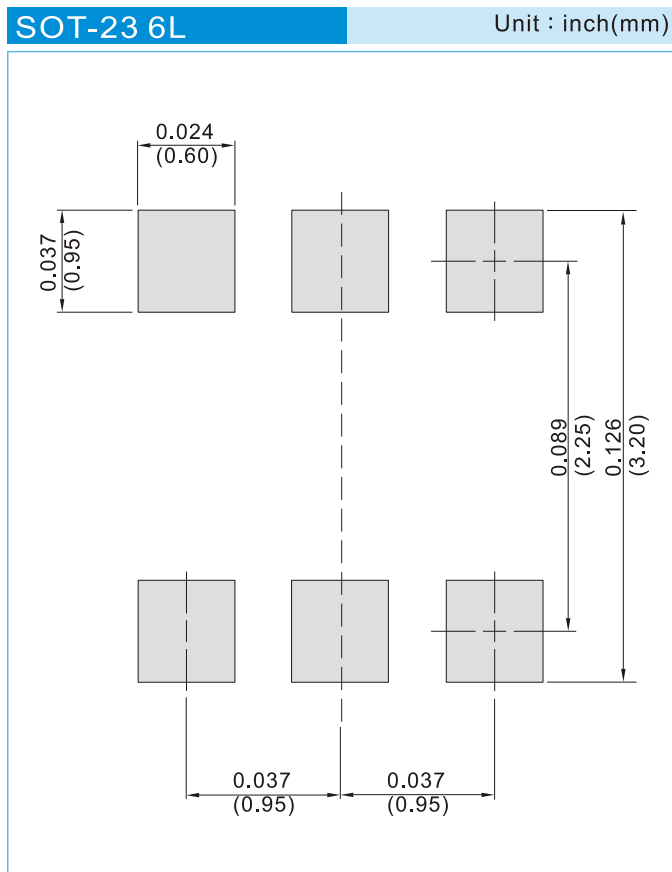


PJS6600

PART NO. PACKING CODE VERSION

| Part No. Packing Code | Package Type | Packing Type | Marking | Version |
|-----------------------|--------------|--------------------|---------|--------------------------------|
| PJS6600_S1_00001 | SOT-23 6L | 3K pcs / 7" reel | SC0 | Halogen free RoHS compliant |
| PJS6600_S2_00001 | SOT-23 6L | 10K pcs / 13" reel | SC0 | Halogen free RoHS compliant |

MOUNTING PAD LAYOUT





PJS6600

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